MOSFET SiC Driver Dedicated Power Supply QA121C2



MOSFET SiC Driver Dedicated Power Supply





FEATURES

- High efficiency up to 81%
- SIP package
- Isolation voltage: 3.5kVAC
- Ultra low isolation capacitance
- Operating temperature range: -40 $^{\circ}$ C to +105 $^{\circ}$ C
- Continuous short circuit protection
- International standard pin-out

Patent Protection RoHS

QA121C2 is DC-DC module power supplie designed for MOSFET SiC driver requiring two set of isolation power supply. The mode of mutual connection after two independent outputs is adopted internally for better energy provision of SiC turn-on and turn-off. Output short circuit protection and self-recovery capabilities are also provided. General application includes:

- 1.Universal converter
- 2.AC servo drive system
- 3.Electric welding machine
- 4.Uninterruptible power supply (UPS)

Selection Guide					
	Input Voltage (VDC)	Output		Efficiency	Many Comparable to
Part No.	Nominal (Range)	Output Voltage (VDC)+Vo/-Vo	Output Current (mA)+lo/-lo	(%,Min./Typ.) @ Full Load	Max. Capacitive Load*(µF)
QA121C2	12 (10.8-13.2)	+15/-3.5	+111/-111	77/81	220

Input Specifications					
Item	Operating Conditions	Min.	Тур.	Max.	Unit
Input Current (full load / no-load)	12V input		210/15		mA
Surge Voltage (1sec. max.)		-0.7	-	18	VDC
Input Filter Capacitor		itor filter			
Hot Plug		Unavailable			

Item	Operating Conditions		Min.	Тур.	Max.	Unit
Outhor th \ /albarasa	Vin=12VDC, Pin6 & Pin7 +lo=+111mA	+Vo	14.4	15	15.9	VDC
Output Voltage	Vin=12VDC, Pin5 & Pin6 -lo=-111mA	-Vo	-3.3	-3.5 -4.0		VDC
	Vin=12VDC, Pin6 & Pin7 +lo=+111mA +Vo -4% to +6%			+6%		
Output Voltage Accuracy	Vin=12VDC, Pin5 & Pin6 -lo=-111mA -Vo -5% to +15%		+15%	5%		
	10%-100% load		See tolerance envelope curve (Fig. 1)			
Line Regulation	Input voltage change: ±1%		-	±1.1	±1.2	%/%
Load Regulation	10%-100% load	+Vo		7		%
Load Regulation	10 %-100 % 10dd	-Vo		10		
Dimula 9. Naisa*	COM I by the group of the deliber	+Vo		120		mVp-p
Ripple & Noise*	20MHz bandwidth	-Vo		80	-	
Temperature Drift Coefficient	100% load		-	±0.02		%/℃
Output Short Circuit Protection				Continuous,	self-recovery	, /

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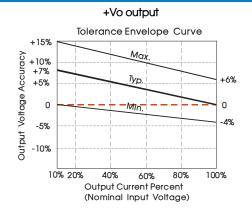


General Specification	ons				
Item	Operating Conditions Min.		Тур.	Max.	Unit
Isolation Voltage	Input-output, with the test time of 1 minute and the leak current lower than 1mA			VAC	
Insulation Resistance	Input-output, isolation voltage 500VDC	Input-output, isolation voltage 500VDC 1000			M Ω
Isolation Capacitance	Input-output, 100KHz/0.1V		3.5	-	рF
Operating Temperature	Derating when operating temperature up to 85° C, (see Fig. 2)	-40		105	
Storage Temperature		-55		125	°C
Pin Welding Resistance Temperature	Welding spot is 1.5mm away from the casing, 10 seconds			300	
Casing Temperature Rise	Ta=25°C		30		
Storage Humidity	Non-condensing			95	%RH
Switching Frequency	100% load, nominal input voltage		67		KHz
MTBF	MIL-HDFK-217F@25℃			-	K hours

Physical Specifications		
Casing Material	Black flame-retardant and heat-resistant plastic	
Dimensions	19.50*9.80*12.50mm	
Weight	4.2g (Typ.)	
Cooling Method	Free air convection	

EMC Specifications			
EMI	CE	CISPR32/EN55032 CLASS B (see Fig. 5 for recommended circuit)	
	RE	CISPR32/EN55032 CLASS B (see Fig. 5 for recommended circuit)	
EMS	ESD	IEC/EN61000-4-2 Contact ±6KV perf. Criteria B	

Product Characteristic Curve



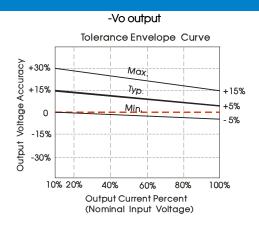
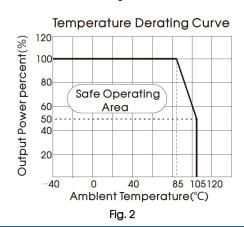


Fig. 1



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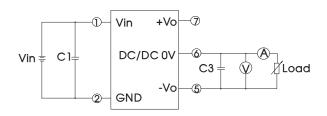


Design Reference

1. Overload Protection

In normal operating conditions, the circuit of these products have no overload protection. Protect with a breaker is a simple way to make overload protection.

2. Test configurations



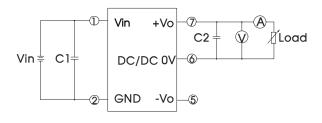
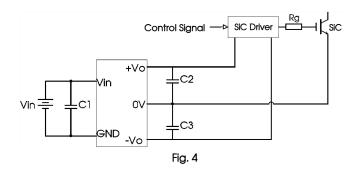


Fig. 3

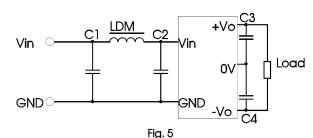
Note: C1,C2,C3: 100uF/35V (Low internal resistance capacitance)

3. Typical application



C1/C2/C3
100uF/35V (Low internal resistance capacitance)

4. EMC typical recommended circuit

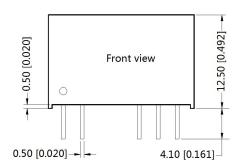


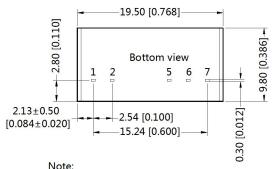
Input voltage (VDC)		15
EMI	C1/C2	4.7µF /50V
	C3/C4	100µF /35V (Low internal resistance capacitance)
	LDM	6.8µH

- 5. The input and the output of the product are recommended to be connected to electrolytic capacitor. Using tantalum capacitor may cause risk of failure
- 6. The product does not support output in parallel with power per liter
- 7. For more information please find the application notes on www.mornsun-power.com



Dimensions and Recommended Layout

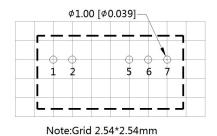




Unit :mm[inch]

Pin section tolerances:±0.10[±0.004] General tolerances:±0.25[±0.010]





Pin-Out			
Pin	Function		
1	Vin		
2	GND		
5	-Vo		
6	0V		
7	+Vo		

Notes:

- Packing information please refer to Product Packing Information which can be downloaded from www.mornsun-power.com. Packing bag number: 58200013;
- 2. The lead connecting the power supply module and SiC driver should be as short as possible during use;
- 3. The output filtering capacitor should be as close as possible to the power supply module and SiC driver;
- 4. The peak of the MOSFET SiC driver dedicated power supply gate drive current is high, so low internal resistance electrolytic capacitor is recommended to be used for the power supply module output filter capacitor;
- 5. The average output power of the driver must be lower than that of the power supply module;
- 6. Consider fixing with glue near the module if being used in vibration occasion;
- 7. The max. capacitive load should be tested within the input voltage range and under full load conditions;
- 8. Unless otherwise specified, data in this datasheet should be tested under the conditions of Ta=25° C, humidity<75% when inputting nominal voltage and outputting rated load;
- 9. All index testing methods in this datasheet are based on our Company's corporate standards;
- 10. The performance indexes of the product models listed in this manual are as above, please directly contact our technicians for specific information;
- 11. We can provide product customization service;
- 12. Specifications of this product are subject to changes without prior notice.

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